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Title: The dynamic three-dimensional models GaAs

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The article discusses the dynamic three-dimensional modeling compounds A3B5. The initial structure is taken compound GaAs. The resulting model is given for different distances from the central atom. There are the distances from one to six. The result is an uneven growth of the number of atoms grouped along the radius of coverage. For the other elements of the possibility of uniform methods increase the number of atoms, such as Ga. To compound semiconductor type A3B5 is GaAs. Its crystal structure are two face-centered cubic lattice, which are shifted relative to each other by º the space diagonal. In the center of origin of the As atoms there are four nearest neighbors at the vertices of a tetrahedron. Each ion is surrounded by four nearest-neighbor ions, the antithesis of the mark. At a distance, there are four ion with qiqj = -1, eight ions antithesis sign qiqj = +1 at a distance. The system ties of the GaAs creates the order of the atomic cores of the tetrahedral combinations. The figure shows the As atoms and Ga for the radius of coverage 6. Red marked atoms As, in blue denote atoms Ga. Central atom is As.